



N-Channel Super Junction Power MOSFET II

General Description

The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

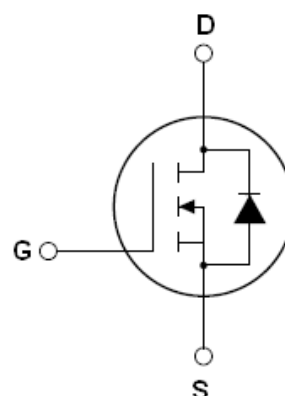
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

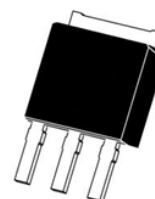
V_{DS}	700	V
$R_{DS(ON)TYP.}$	840	m Ω
I_D	5	A



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
TGD70R900L	TO-251S	TGD70R900L



TO-251S

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	700	V
Gate-Source Voltage ($V_{DS}=0V$)	V_{GS}	± 30	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	5	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	3	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	15	A
Drain Source voltage slope, $V_{DS} = 480\text{ V}$, $I_D = 5\text{ A}$, $T_j = 125^\circ\text{C}$	dv/dt	48	V/ns
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	49	W
Derate above 25°C		0.39	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note2)	E_{AS}	135	mJ
Avalanche current (Note 1)	I_{AR}	2.5	A



Parameter	Symbol	Value	Unit
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.4	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	2.55	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	75	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	700			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =700V,V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =700V,V _{GS} =0V			50	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±30V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	2.5	3	3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2.5A		840	950	mΩ
Dynamic Characteristics						
Forward Transconductance	g _{FS}	V _{DS} = 20V, I _D = 3A		4.8		S
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz		460		pF
Output Capacitance	C _{oss}			45		pF
Reverse Transfer Capacitance	C _{rss}			3.5		pF
Total Gate Charge	Q _g	V _{DS} =480V,I _D =5A, V _{GS} =10V		10	20	nC
Gate-Source Charge	Q _{gs}			1.6		nC
Gate-Drain Charge	Q _{gd}			4		nC
Intrinsic gate resistance	R _G	f = 1 MHz open drain		2.5		Ω
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V,I _D =3A, R _G =18Ω,V _{GS} =10V		6		nS
Turn-on Rise Time	t _r			3		nS
Turn-Off Delay Time	t _{d(off)}			50	60	nS
Turn-Off Fall Time	t _f			9	15	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			5	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				15	A
Forward on voltage	V _{SD}	T _j =25℃,I _{SD} =5A,V _{GS} =0V		1	1.3	V
Reverse Recovery Time	t _{rr}	T _j =25℃,I _F =5A,di/dt=100A/μs		250		nS
Reverse Recovery Charge	Q _{rr}			2.2		uC
Peak reverse recovery current	I _{rrm}			15		A

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

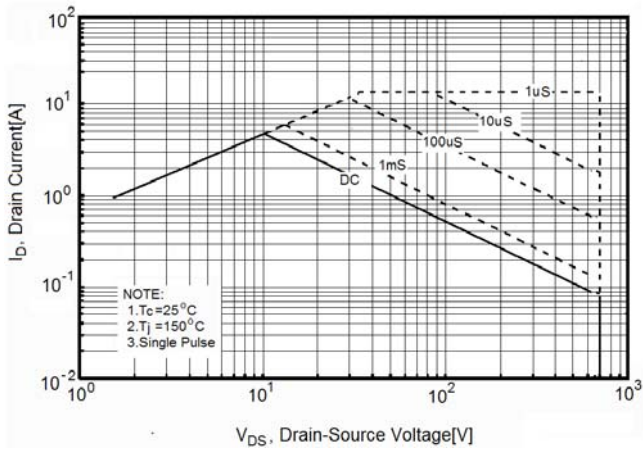
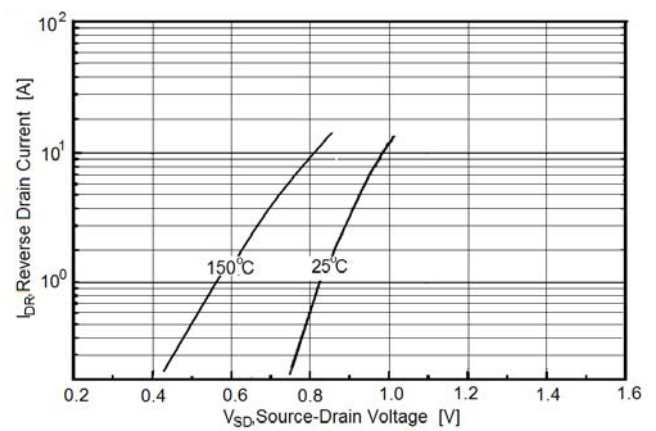
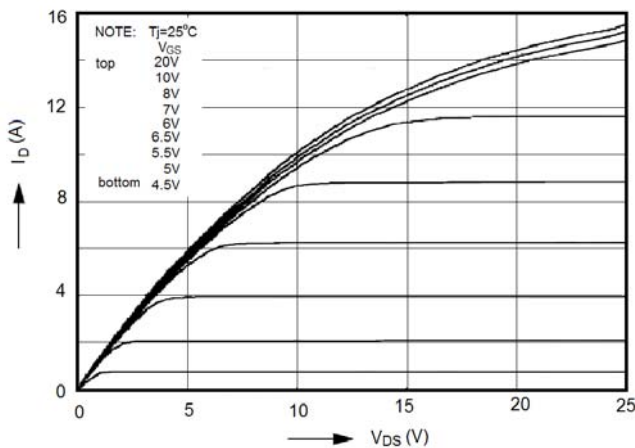
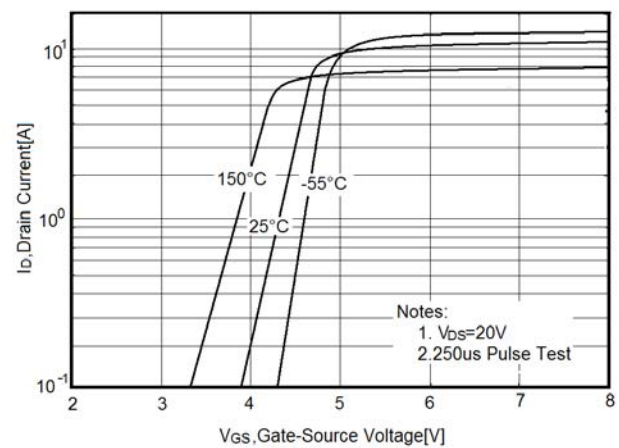
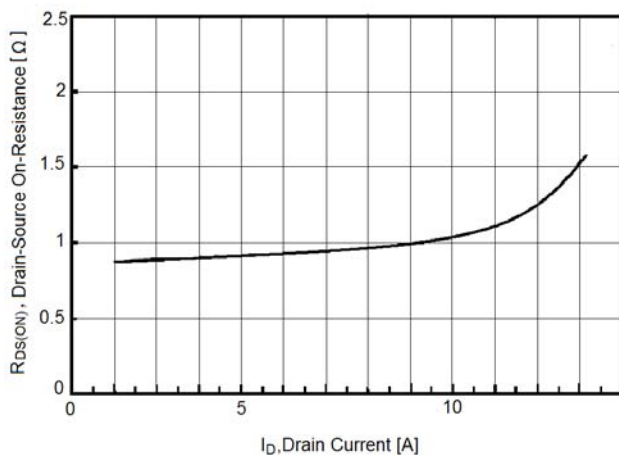
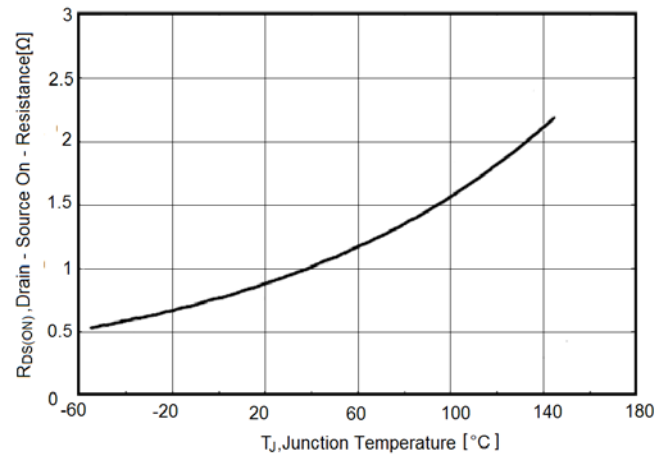
Figure1. Safe operating area

Figure2. Source-Drain Diode Forward Voltage

Figure3. Output characteristics

Figure4. Transfer characteristics

Figure5. Static drain-source on resistance

Figure6. $R_{DS(ON)}$ vs Junction Temperature


Figure7. BV_{DSS} vs Junction Temperature

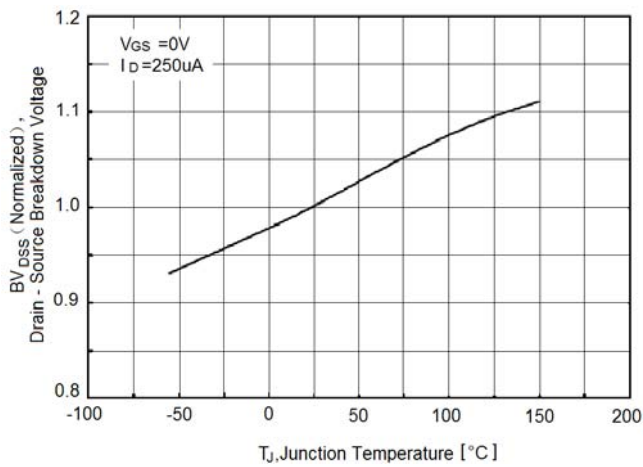


Figure8. Maximum I_D vs Junction Temperature

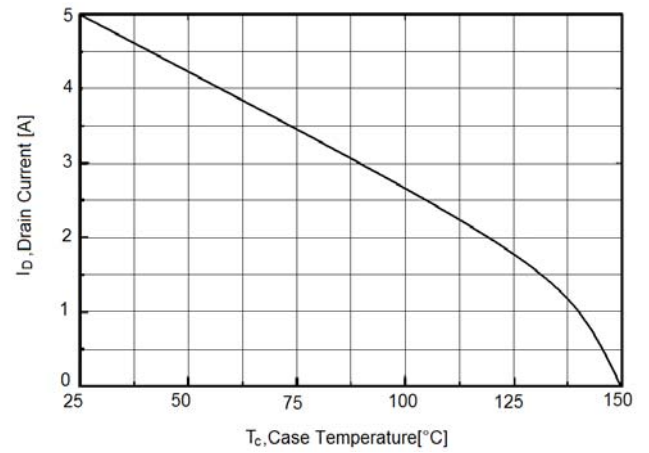


Figure9. Gate charge waveforms

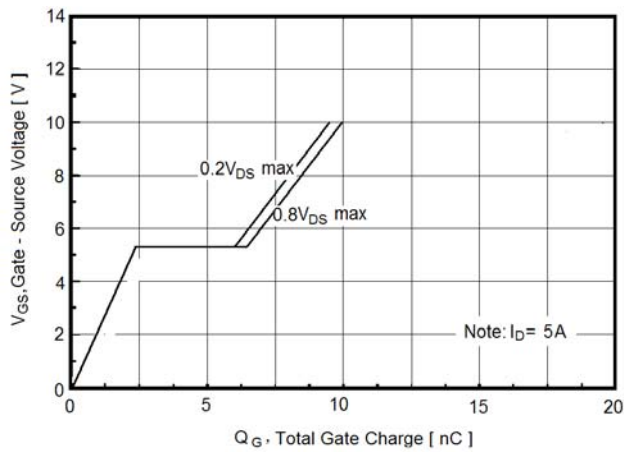


Figure10. Capacitance

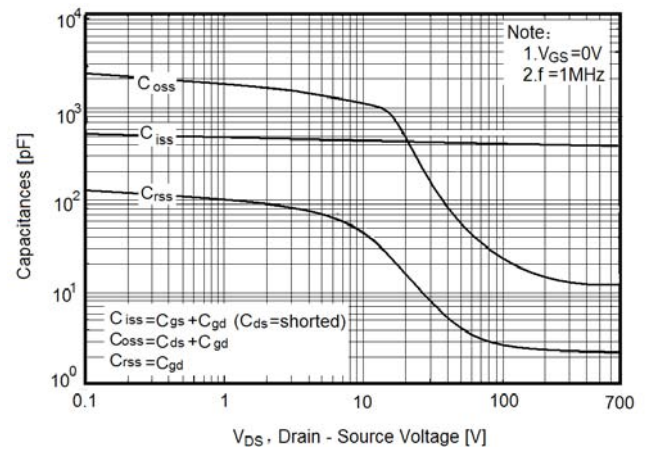
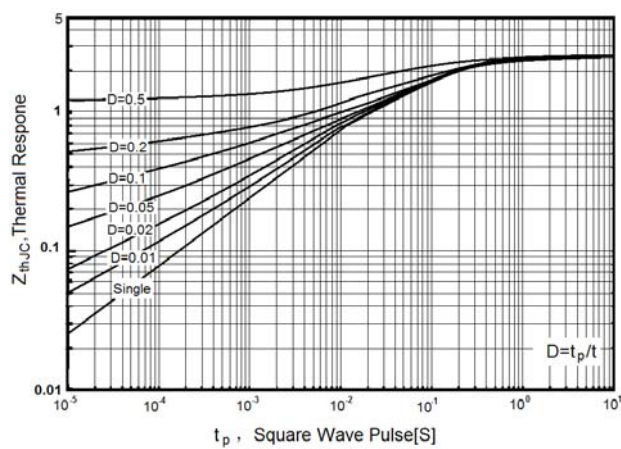
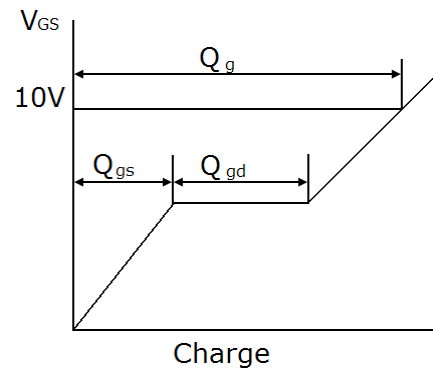
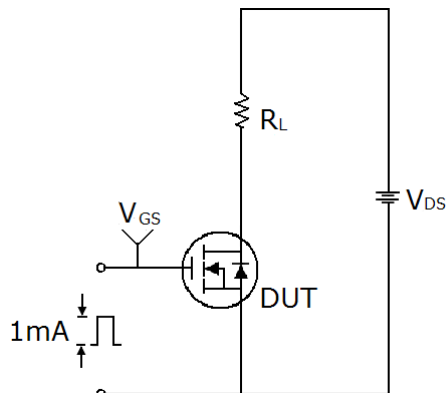


Figure11. Transient Thermal Impedance

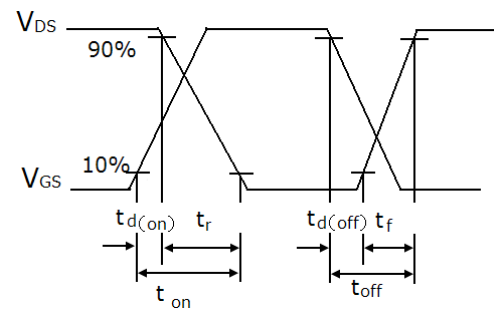
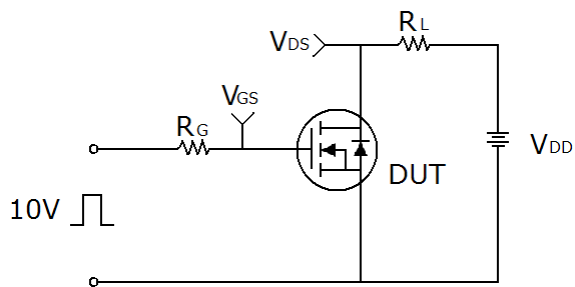


Test circuit

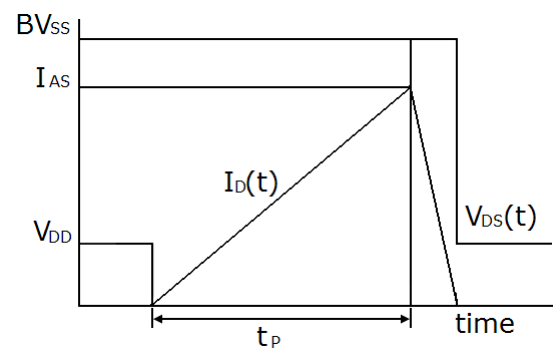
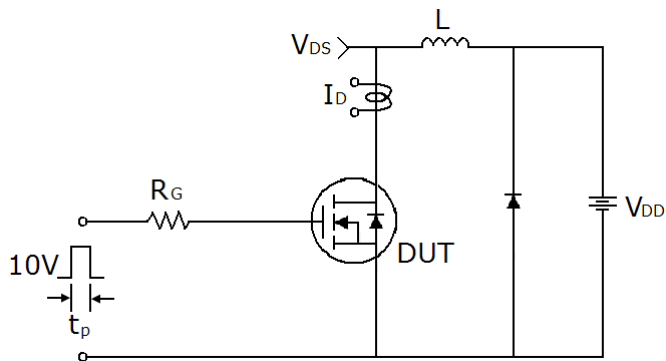
1) Gate charge test circuit & Waveform



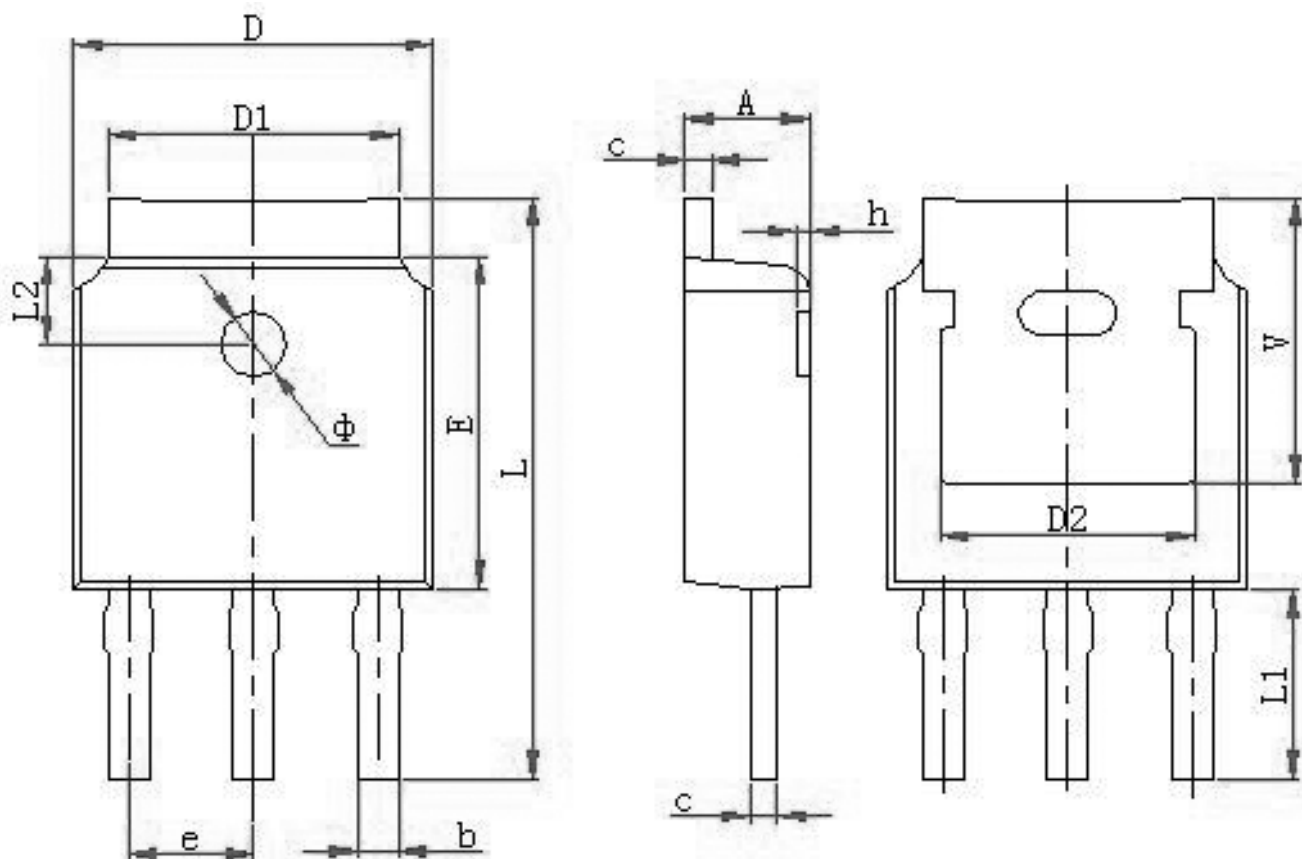
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms



TO-251S Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	10.400	11.000	0.409	0.433
L1	3.300	3.700	0.130	0.146
L2	1.600 REF.		0.063 REF.	
Φ	1.100	1.300	0.043	0.051
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	